



KA5Q0565RT

Fairchild Power Switch(FPS)

Features

- Quasi Resonant Converter Controller
- Internal Burst Mode Controller for Stand-by Mode
- Pulse by Pulse Current Limiting
- Over Current Latch Protection
- Over Voltage Protection (Vcc: Min. 27V)
- Internal Thermal Shutdown Function
- Under Voltage Lockout
- Internal High Voltage Sense FET
- Auto-Restart Mode

Description

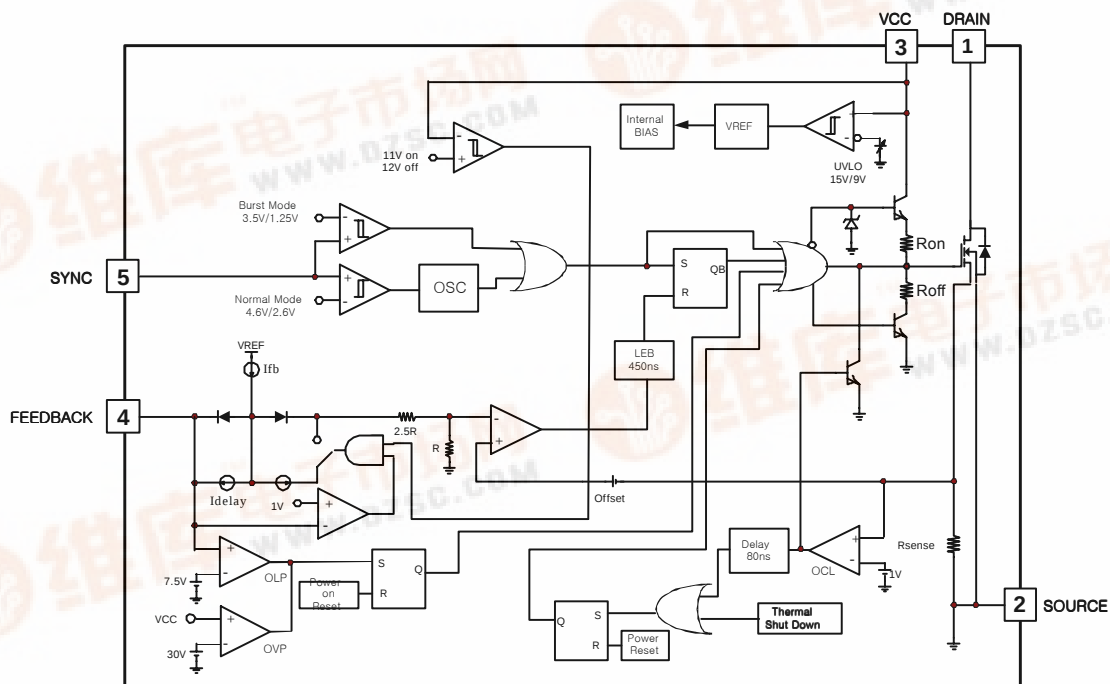
The Fairchild Power Switch(FPS) product family is specially designed for an off-line SMPS with minimal external components. The Fairchild Power Switch(FPS) consists of a high voltage power SenseFET and a current mode PWM IC. The integrated PWM controller includes the fixed oscillator, the under voltage lock out, the leading edge blanking, the optimized gate turn-on/turn-off driver, the thermal shut down protection, the over voltage protection, and the temperature compensated precision current sources for loop compensation and fault protection circuitry. Compared to a discrete MOSFET and a controller or a RCC switching converter solutions, a Fairchild Power Switch(FPS) can reduce the total number of components, design size, and weight, so it will improve efficiency, productivity, and system reliability. It has a basic platform well suited for cost-effective design in a quasi-resonant converter as a C-TV power supply.

TO-220F-5L



1. Drain 2. GND 3. Vcc
4. Feedback 5. Sync

Internal Block Diagram



Absolute Maximum Ratings

(Ta=25°C, unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-source Voltage	VDSS	650	V
Drain-Gate Voltage (RGS=1MΩ)	VDGR	650	V
Gate-Source (GND) Voltage	VGS	±30	V
Drain Current Pulsed ⁽²⁾	IDM	11	ADC
Single Pulsed Avalanche Current ⁽³⁾ (Energy ⁽²⁾)	IAS(EAS)	13(400)	A(mJ)
Continuous Drain Current (Tc = 25°C)	ID	2.8	ADC
Continuous Drain Current (TC=100°C)	ID	1.7	ADC
Supply Voltage	VCC	30	V
Input Voltage Range	VFB	-0.3 to Vcc	V
Total Power Dissipation	PD	38	W
	Derating	0.3	W/°C
Operating Junction Temperature	TJ	+160	°C
Operating Ambient Temperature	TA	-25 to +85	°C
Storage Temperature Range	TSTG	-55 to +150	°C
Thermal Resistance	Rthjc	3.29	°C/W
ESD Capability, HBM Model (All pins)	-	2.0	kV
ESD Capability, Machine Model (All pins)	-	300	V

Notes:

1. Tj = 25°C to 150°C
2. Repetitive rating: Pulse width limited by maximum junction temperature
3. L = 30mH, VDD = 50V, RG = 25Ω, starting Tj = 25°C
4. L = 13uH, starting Tj = 25°C

Electrical Characteristics (SFET Part)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BVDSS	V _{GS} = 0V, I _D = 50μA	650	-	-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} = Max, Rating, V _{GS} = 0V	-	-	200	μA
		V _{DS} = 0.8*Max., Rating V _{GS} = 0V, T _C = 85°C	-	-	300	μA
Static Drain-source on Resistance ^(Note)	RDS(ON)	V _{GS} = 10V, I _D = 2.3A	-	1.8	2.2	Ω
Input Capacitance	Ciss	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz	-	780	-	pF
Output Capacitance	Coss		-	90	-	
Reverse Transfer Capacitance	Crss		-	40	-	
Turn on Delay Time	td(on)	V _{DD} = 0.5BVDSS, I _D = 7.0A (MOSFET switching time are essentially independent of operating temperature)	-	15	40	nS
Rise Time	tr		-	45	100	
Turn Off Delay Time	td(off)		-	60	130	
Fall Time	tf		-	40	90	
Total Gate Charge (Gate-Source+Gate-Drain)	Qg	V _{GS} = 10V, I _D = 7.0A, V _{DS} = 0.5B V _{DSS} (MOSFET Switching time are Essentially independent of operating temperature)	-	43	55	nC
Gate-Source Charge	Qgs		-	4.0	-	
Gate-Drain (Miller) Charge	Qgd		-	7.3	-	

Note:

1. Pulse test : Pulse width ≤ 300μS, duty ≤ 2%

Electrical Characteristics (Continued)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
UVLO SECTION						
Start Threshold Voltage	V _{START}	V _{FB} = GND	14	15	16	V
Stop Threshold Voltage	V _{STOP}	V _{FB} = GND	8	9	10	V
OSCILLATOR SECTION						
Initial Frequency	F _{OSC}	-	18	20	22	kHz
Voltage Stability	F _{STABLE}	12V ≤ V _{CC} ≤ 23V	0	1	3	%
Temperature Stability (Note2)	ΔF _{OSC}	-25°C ≤ Ta ≤ 85°C	0	±5	±10	%
Maximum Duty Cycle	D _{MAX}	-	92	95	98	%
Minimum Duty Cycle	D _{MIN}	-	-	-	0	%
FEEDBACK SECTION						
Feedback Source Current	I _{FB}	V _{FB} = GND	0.7	0.9	1.1	mA
Shutdown Feedback Voltage	V _{SD}	V _{fb} ≥ 6.9V	6.9	7.5	8.1	V
Shutdown Delay Current	I _{DELAY}	V _{FB} = 5V	4	5	6	μA
PROTECTION SECTION						
Over Voltage Protection	V _{CCOVP}	V _{CC} ≥ 26V	27	30	33	V
Over Current Latch Voltage (Note2)	V _{OCL}	-	0.9	1.0	1.1	V
Thermal Shutdown Temp.	T _{SD}	-	140	160	-	°C
SYNC SECTION						
Normal Sync High Threshold Voltage	V _{NSH}	V _{CC} = 16V, V _{fb} = 5V	4.0	4.6	5.2	V
Normal Sync Low Threshold Voltage	V _{NSL}	V _{CC} = 16V, V _{fb} = 5V	2.3	2.6	2.9	V
Burst Sync High Threshold Voltage	V _{BSH}	V _{CC} = 10.5V, V _{fb} = 0V	3.2	3.6	4.0	V
Burst Sync Low Threshold Voltage	V _{BSL}	V _{CC} = 10.5V, V _{fb} = 0V	1.1	1.3	1.5	V

Note:

1. These parameters is the current flowing in the Control IC.
2. These parameters, although guaranteed, are tested in EDS(wafer test) process.
3. These parameters indicate Inductor Current.

Electrical Characteristics (Continued)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
BURST MODE SECTION						
Burst Mode Low Threshold Voltage	VBURL	Vfb = 0V	10.4	11.0	11.6	V
Burst Mode High Threshold Voltage	VBURH	Vfb = 0V	11.4	12.0	12.6	V
Burst Mode Enable Feedback Voltage	VBEN	Vcc = 10.5V	0.7	1.0	1.3	V
Burst Mode Peak Current Limit	IBU_PK	Vcc = 10.5V	0.65	0.85	1.1	A
CURRENT LIMIT(SELF-PROTECTION)SECTION						
Peak Current Limit(Note3)	IPK	-	3.08	3.5	3.92	A
TOTAL DEVICE SECTION						
Start Up Current	ISTART	Vfb = GND, VCC = 14V	-	0.1	0.2	mA
Operating Supply Current (Note1)	IOP	Vfb = GND, VCC = 16V	-	10	18	mA
	IOP(MIN)	Vfb = GND, VCC = 10V				
	IOP(MAX)	Vfb = GND, VCC = 28V				

Note:

1. These parameters is the current flowing in the Control IC.
2. These parameters, although guaranteed, are tested in EDS(wafer test) process.
3. These parameters indicate Inductor Current.

Typical Performance Characteristics

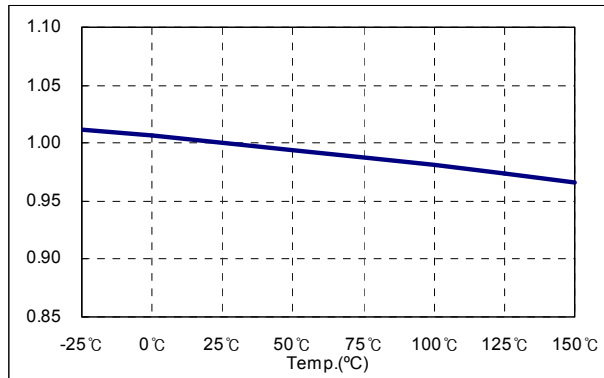


Figure 1. Start Voltage

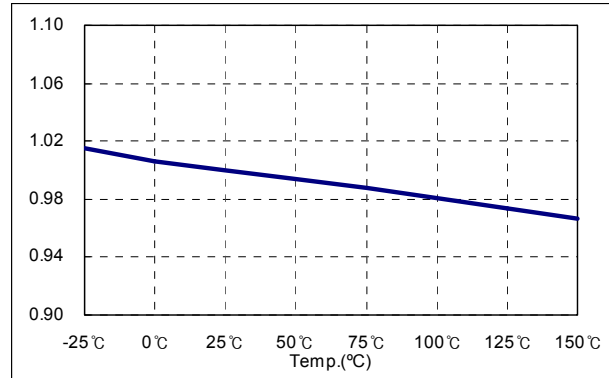


Figure 2. Stop Voltage

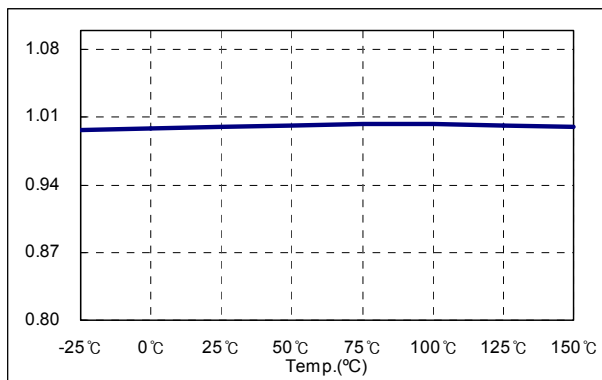


Figure 3. Stand by Current

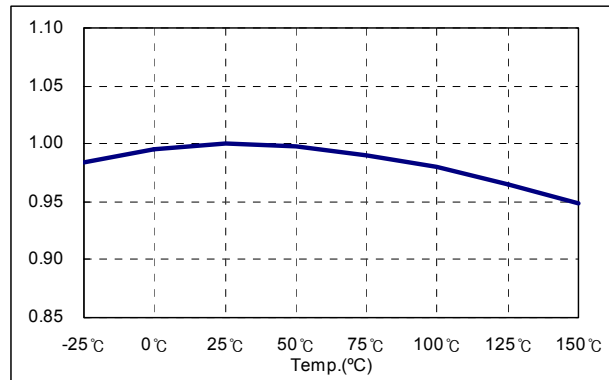


Figure 4. Operating Current

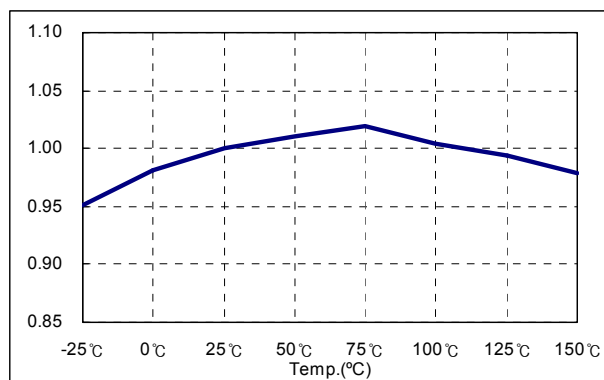


Figure 5. Initial Frequency

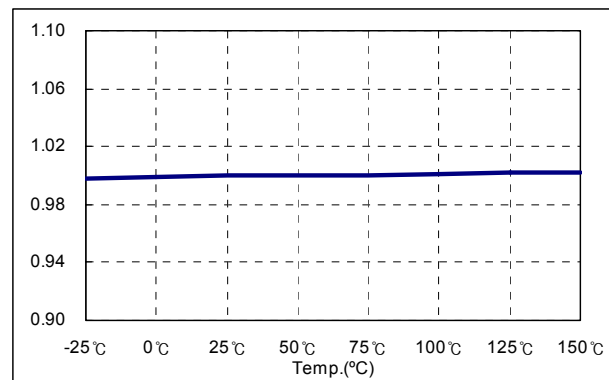


Figure 6. Maximum Duty

Typical Performance Characteristics (Continued)

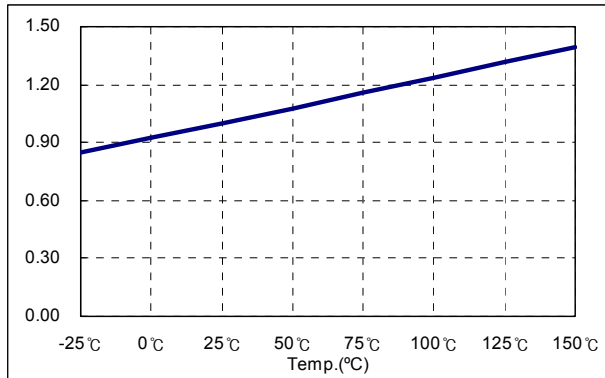


Figure 7. Feedback Offset Voltage

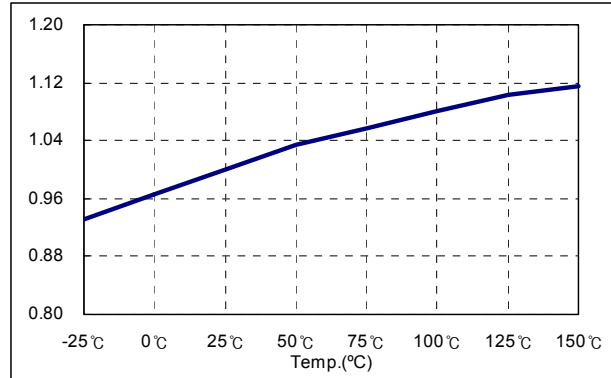


Figure 8. Feedback Source Current

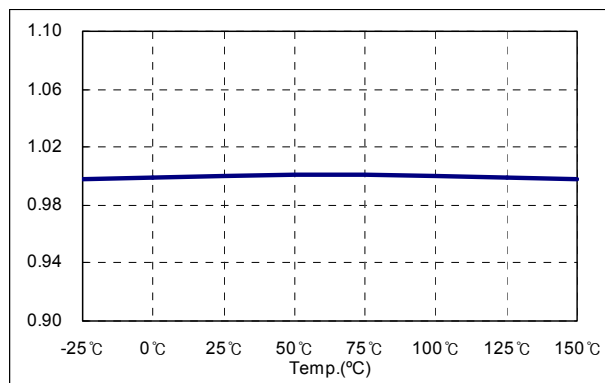


Figure 9. Over Voltage Protection

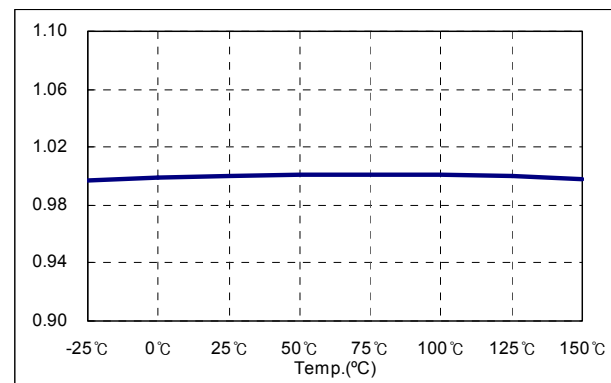


Figure 10. Shutdown Feedback Voltage

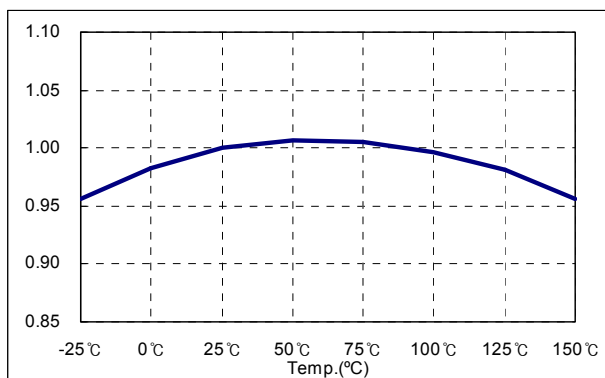


Figure 11. ShutDown Delay Current

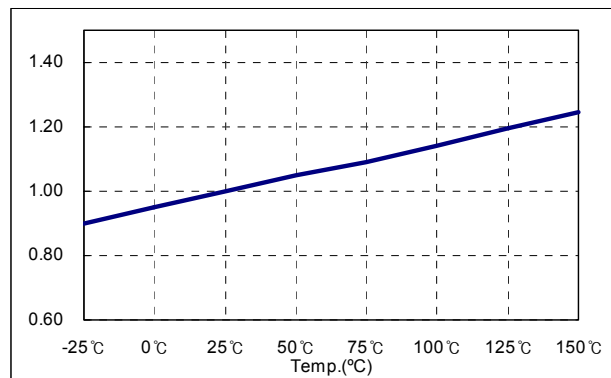


Figure 12. Burst Mode Enable Feedback Voltage

Typical Performance Characteristics (Continued)

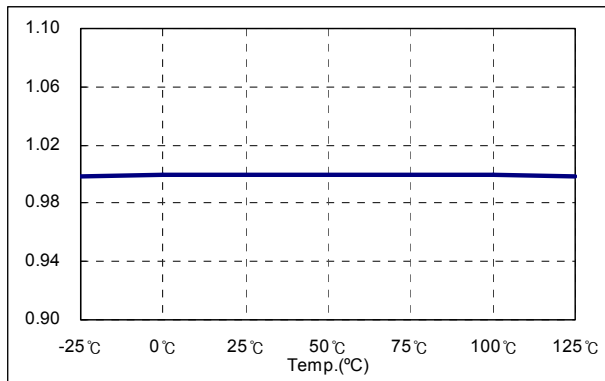


Figure 13. Burst Mode Low Threshold Voltage

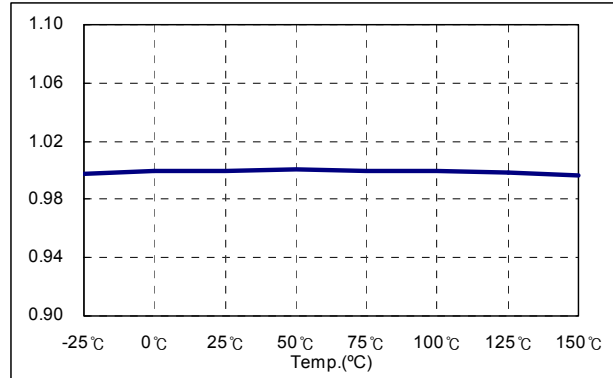


Figure 14. Burst Mode High Threshold Voltage

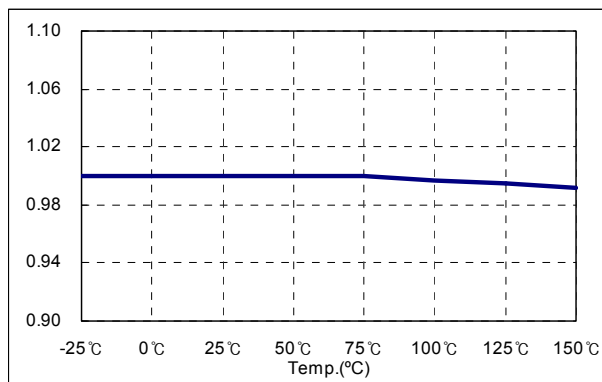


Figure 15. Burst Mode Sync. High Threshold Voltage

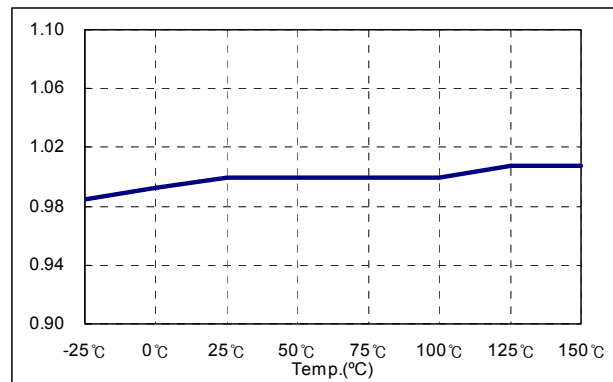


Figure 16. Burst Mode Sync. Low Threshold Voltage

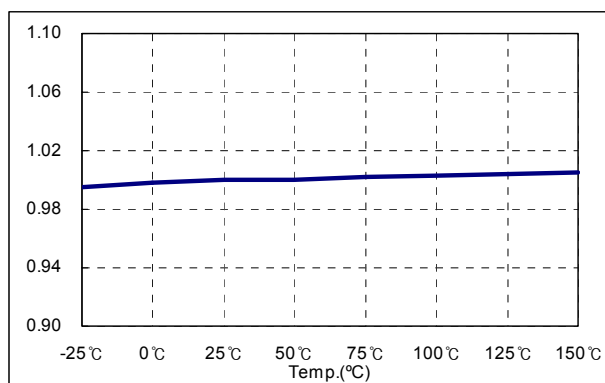


Figure 17. Primary Voltage

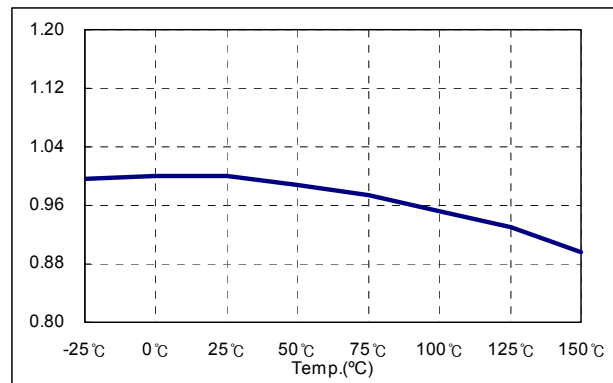


Figure 18. Primary Mode Gain

Typical Performance Characteristics (Continued)

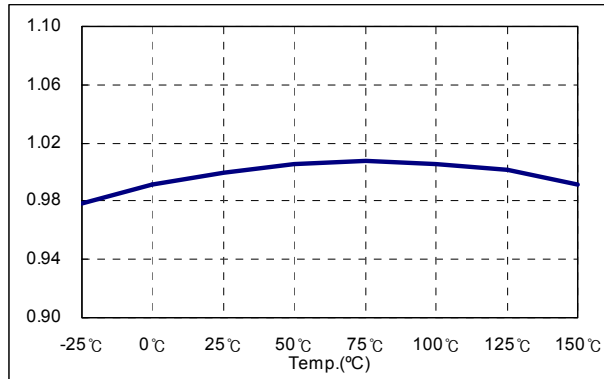


Figure 19. Peak Current Limit

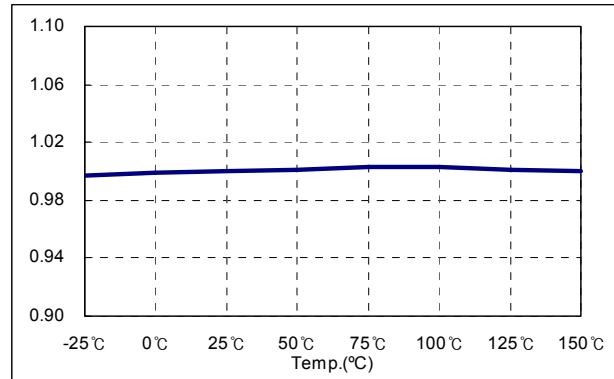


Figure 20. Burst Mode Peak Current Limit

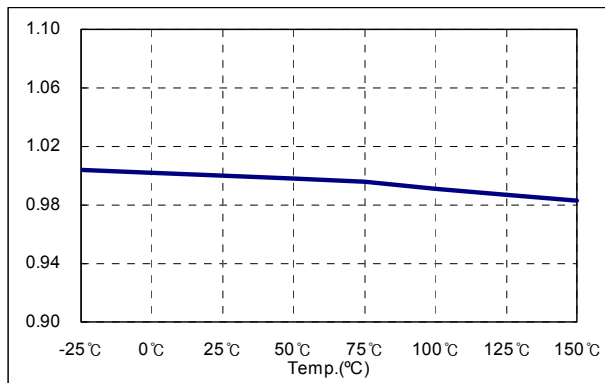


Figure 21. Normal Mode Sync. High Threshold Voltage

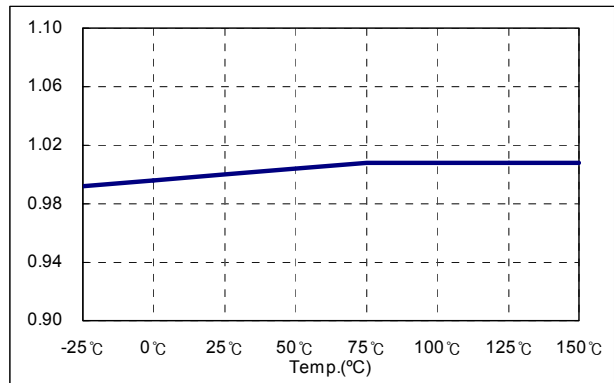


Figure 21. Normal Mode Sync. Low Threshold Voltage

Typical Performance Characteristics (MOSFET Part)

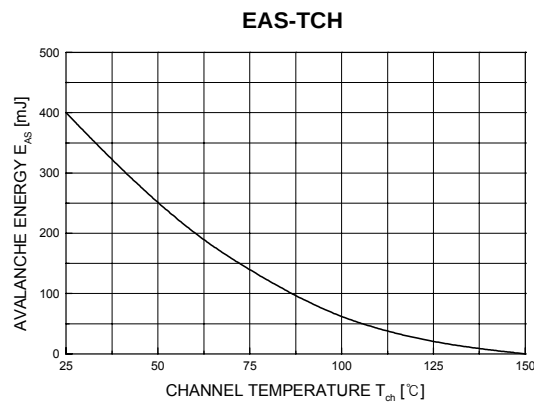


Figure 22. Temperature (T_C) vs. Eas Curve

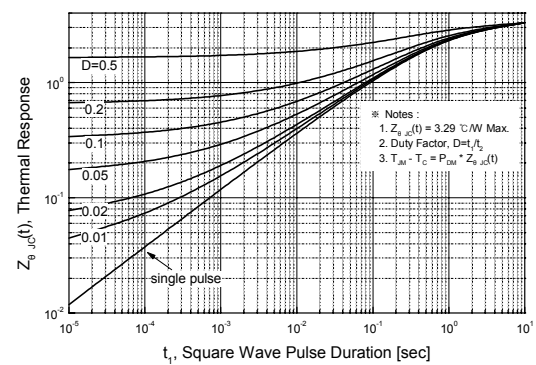


Figure 23. Transient Thermal Response Curve

Ordering Information

Product Number	Package	Operating Temp.
KA5Q0565RTTU	TO-220F-5L	-25°C to +85°C
KA5Q0565RTYDTU	TO-220F-5L(Forming)	

TU : Non Forming Type

YDTU : Forming Type

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2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.